The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A semiconductor device comprising:

a translucent substrate;

a base film having a region of a first thickness and a region of a second thickness smaller than the first thickness, the film being formed over one surface of the translucent substrate, and the region of the first thickness having an area smaller than the region of the second thickness; and

an island-like semiconductor layer having a crystal structure over the base film, the layer being formed over the region of the first thickness and the region of the second thickness.

2. (New) A semiconductor device comprising a translucent substrate and a thin film transistor over the translucent substrate, wherein

a base film having a region of a first thickness and a region of a second thickness smaller than the first thickness is provided over one surface of the translucent substrate;

the region of the first thickness has an area smaller than the region of the second thickness; and

at least a part of a channel formation region of the thin film transistor is provided over the region of the first thickness.

3. (New) A semiconductor device according to claim 1, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

4. (New) A semiconductor device according to claim 2, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

5. (New) A semiconductor device comprising:

a translucent substrate;

a heat conduction layer formed like an island over one surface of the translucent substrate;

a base film over the translucent substrate, the base film being formed to cover the heat conduction layer; and

an island-like semiconductor layer having a crystal structure over the base film, at least a part of the island-like semiconductor layer being formed over the heat conduction layer.

6. (New) A semiconductor device in which a thin film transistor is provided over a translucent substrate, the semiconductor device comprising:

a heat conduction layer formed like an island over one surface of the translucent substrate; and

a base film over the translucent substrate, the base film being formed to cover the heat conduction layer;

wherein at least a part of a channel formation region of the thin film transistor is provided over the heat conduction layer.

7. (New) A semiconductor device according to claim 5, wherein the heat conduction layer contains at least one selected from the group consisting of aluminum oxide, aluminum nitride, and aluminum nitride oxide.

8. (New) A semiconductor device according to claim 6, wherein the heat conduction layer contains at least one selected from the group consisting of aluminum oxide, aluminum nitride, and aluminum nitride oxide.

9. (New) A semiconductor device according to claim 5, wherein the heat conduction layer includes a compound containing Si, N, O and M, M being at least one selected from the group consisting of Al and rare earth elements.

10. (New) A semiconductor device according to claim 6, wherein the heat conduction layer includes a compound containing Si, N, O and M, M being at least one selected from the group consisting of Al and rare earth elements.